

Research Status of Laser Cutting Technology

Chenwei Li¹, Shufeng Sun²

¹Discipline Innovation and Wisdom Introduction Base of High-end Laser Intelligent Manufacturing Technology and Equipment, Qingdao University of Technology, Qingdao 266525, China

²Shandong Provincial Key Laboratory of High-end Laser Manufacturing Technology and Equipment, Qingdao University of Technology, Qingdao 266525, China

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Abstract

With the highly advanced development, high performance of integrated circuit manufacturing, and rapid advancement of optoelectronic technology, hard and brittle transparent materials such as silicon wafers and quartz glass have been widely used in fields including integrated circuits, micro-electromechanical systems, and aero-space, thanks to their excellent physicochemical properties. The dicing quality of silicon wafers plays a decisive role in the final product quality and economic benefits; similarly, quartz glass also requires high-quality dicing to prevent stress from propagating along the defective parts of the glass edges and thus causing cracking. This study investigated the current status of dicing from three aspects: traditional dicing, assisted dicing, and dicing after spatial light modulation (SLM). Meanwhile, the factors influencing dicing were studied from the perspectives of laser types, laser polarization states, processing parameters, and processing technologies.

Keywords

Cutting Technology; Traditional Cutting; New-Type Laser-Cutting

1. Introduction

Since the 21st century, lasers have become one of the fastest-developing green technologies and among humanity's most important inventions. Since their discovery in 1960, lasers have developed rapidly, breathing new life into traditional optical science and spawning new industries[1]. The application fields of transparent materials are constantly expanding, covering microelectronics, microfluidics, optoelectronic, and other domains.

Owing to its excellent electrical and mechanical properties, silicon has made silicon wafers the most commonly used semiconductor materials today, which are widely applied in the integrated circuit chip industry[2]. Quartz glass possesses a series of outstanding physicochemical properties, such as high-temperature resistance, corrosion resistance, light transmittance, and electrical insulation. Consequently, it is

extensively used in integrated electronics[3], micro-electromechanical systems (MEMS), high-end displays, microchannels, aerospace, and other fields[4]. In the aerospace sector, ring laser gyroscopes made of quartz glass are critical components of aircraft navigation systems, used to measure minor changes in direction[5]. In the semiconductor and data communication fields, quartz glass is a promising material that can replace traditional substrate materials to serve as the substrate for radio frequency (RF) energy harvesting systems based on MEMS technology[6]. The specific applications of silicon wafers and quartz glass in the aforementioned fields are illustrated in Fig1.

Contact-based machining methods make workpieces more sensitive to externally applied mechanical stress. Furthermore, they often require specific liquids for assistance, and dicing defects—such as material contamination, chipping, and cracking—are common. These issues pose significant challenges to traditional tool-based dicing processes[7]. However, despite the growing application of these transparent materials in the consumer electronics field, their brittle nature makes the dicing process extremely challenging. Particularly when processing thinner substrates, achieving a high-quality diced edge completely free of microcracks or fragments remains a challenge.

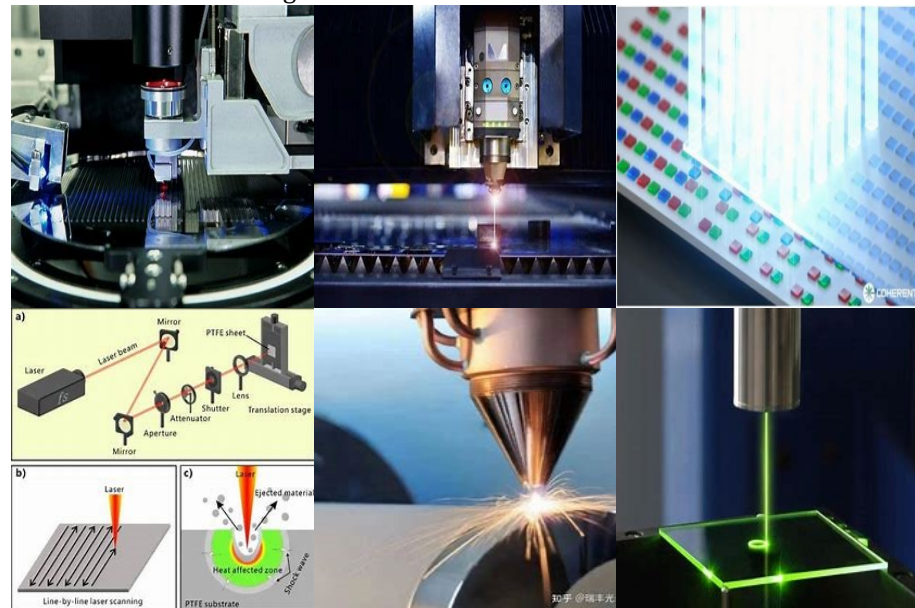


Fig 1. Applications of Laser Machining

Laser cutting technology is a cutting technique that uses lasers to process flat surfaces. Owing to its advantages such as high processing precision and no pollution, it has attracted the attention of many researchers. With the continuous development and progress of science and technology, higher requirements have been put forward for the performance of parts; thus, the methods and equipment for processing parts are constantly updated and improved.

Most traditional parts are manufactured using mechanical machining methods,

which have shortcomings including low processing efficiency and poor environmental friendliness—problems that laser processing has exactly solved. Laser cutting technology utilizes a laser generator to output a laser beam with high energy density. This laser beam scans the processing surface, and the local area of the material undergoes melting and vaporization, enabling rapid shaping[8]. In the field of cutting-edge processing, laser processing has been applied in the design of micro-mechanical structures. It can maintain the dimensional accuracy of micro-structured parts and boasts advantages such as high cutting efficiency, fast speed, good quality, and environmental friendliness[9].

Domestic and international researchers have conducted certain studies on the interaction between lasers and materials, as well as the optimization of laser cutting parameters, which have promoted the development of laser cutting. This paper will introduce the research and development history of laser cutting technology, including the relevant theoretical research on traditional cutting, assisted cutting, and laser cutting after spatial light modulation (SLM). Meanwhile, it will also provide an overview of several factors that affect the cutting process.

2. Traditional Cutting Technology

2.1. Tool-Based Cutting

In traditional cutting technology, mechanical blade cutting is a common method that achieves material separation by applying mechanical force to the workpiece; over its development, dicing saw technology has become highly stable and mature, making it the industry's prevailing wafer cutting method. In semiconductor wafer manufacturing, after devices are fabricated on individual dies, the wafer is typically divided using automated precision dicing saws or scribing machines—this technology has existed since the early days of the semiconductor industry and represents a mature process with sophisticated blade designs, materials, and process recipes[10]. Blade cutting operates via a grinding-like mechanism, where material is sheared from the wafer by fine abrasive particles embedded on the edge of a rotating blade[11]; the cutting blade functions as a thin grinding wheel that rotates at high speed to abrade the wafer, resulting in full or partial penetration through the wafer thickness. However, when the wafer thickness decreases below 100 μm , blade cutting often causes severe wafer damage such as chipping, cracking, delamination, and residual stress in singulated dies, which significantly reduces process yield, and this has become a major challenge as the semiconductor industry trends toward wafers thinner than 100 μm [12]. The earliest wafer cutting technology was mechanical blade cutting, which uses a blade rotating stably at high speed to perform intensive grinding on the wafer while using a coolant to rinse the cutting point—this coolant serves to cool the blade and carry away dust generated during cutting. Yet as wafer thickness continues to decrease, wafers become more brittle and unable to withstand the high-intensity grinding of the blade,

easily fracturing during cutting, damaging chips, and lowering yield. Additionally, blade cutting itself has inherent shortcomings: it is a contact-based cutting method, which inevitably causes edge chipping and peeling on the wafer; the kerf width is large (generally over 100 μm), reducing the effective usable area of the wafer; the blade has a short service life and may break unexpectedly, making maintenance difficult; and the cutting process requires coolant, which increases economic costs, while improper disposal of residual coolant can easily cause environmental pollution. Furthermore, the incorporation of low-k dielectric materials increases wafer brittleness and reduces mechanical performance, making blade cutting prone to peeling, edge chipping, and material detachment—these issues lead to decreased chip performance and low yield. To address the above problems, the industry has begun to develop laser cutting technology [13].

2.2. Traditional Laser Cutting Technology

Lasers used in traditional laser cutting technology include solid-state lasers (e.g., Nd:YAG lasers), gas lasers (e.g., CO_2 lasers), and fiber lasers; the emitted laser can be continuous waves, pulsed waves, or mode-locked waves, with wavelengths ranging from ultraviolet to 10.6 μm (the wavelength of CO_2 lasers) and pulse widths spanning from microseconds to femtoseconds [14]. Through rational selection of these parameters, the cutting objective can be achieved. The dicing speed of wafers is related to the laser operating wavelength: lasers with longer wavelengths enable faster dicing, while those with shorter wavelengths result in slower dicing. Meanwhile, dicing quality is associated with pulse width—during cutting with long-pulse lasers, the interaction time between the material and laser is prolonged, leading to a large heat-affected zone (HAZ), whereas short-pulse lasers produce a smaller HAZ. Typical laser pulse widths include microsecond, nanosecond, and picosecond levels, with corresponding thermal diffusion lengths of 900 μm , 1 μm , and 0.1 μm , respectively; however, lasers with shorter pulse widths are more expensive. C. Fornari et al. conducted dicing experiments on doped silicon wafers with a thickness of 500 μm using a laser with a wavelength of 532 nm and a pulse width of less than 15 ps, achieving a minimum dicing width of 17 μm and a maximum effective dicing speed of 2 mm/s—these are the best results obtained with short-pulse lasers to date. Lasers with a wavelength of 355 nm feature short wavelengths and small pulse widths; they not only enable narrow dicing widths and small HAZs but also achieve relatively high speeds, exhibiting obvious advantages in terms of quality and efficiency. Compared with contact-based blade dicing technology, traditional laser cutting technology offers advantages such as higher dicing speed, more flexible dicing patterns, and higher wafer utilization [15]. However, the thermal effect between the laser and material introduces HAZs and microcracks: an excessively large HAZ reduces the effective usable area of the wafer, and if microcracks extend to the protection range of the chip, the chip's performance will be affected.

Therefore, to address issues such as HAZs and microcracks, two newtypes of laser-cutting technology have been developed based on traditional laser cutting technology—namely, micro water-jet guided laser cutting technology (designed to reduce the HAZ) and stealth dicing technology (developed to effectively control microcracks).

3. New Types of Laser Cutting Technology

3.1. Water-Jet Assisted Cutting Technology

Switzerland-based Synova SA applied the concept of micro water-jet-guided laser to laser cutting and developed micro water-jet guided laser cutting equipment. This equipment mainly consists of four components: a laser system, an optical focusing system, a pressure water chamber, and the total internal reflection propagation module of laser in the water jet [16]. The basic principle of micro water-jet-guided laser technology is that an ultra-thin, low-pressure water jet guides the laser beam to the workpiece for processing. Meanwhile, the water jet plays a cooling role during processing, eliminating the defect of excessively large heat-affected zone (HAZ) in traditional laser cutting.

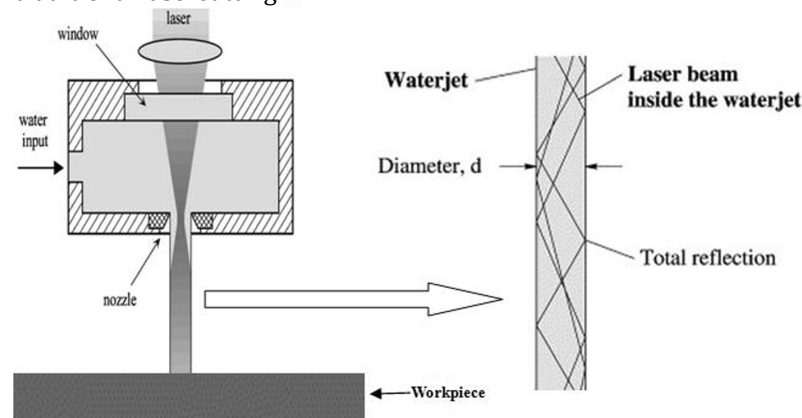


Fig 2. Working Principle of Micro Water-Jet Guided Laser

As shown in Fig.2 [17], the laser beam passing through the focusing lens travels through the window above the pressure water chamber, is focused on the nozzle at the bottom of the pressure water chamber, and then enters the water jet at a certain divergence angle. Through total internal reflection at the water/air interface, the water jet guides the laser beam to the workpiece surface. The nozzle, designed based on fluid mechanics, ensures that the emitted water jet maintains its shape over a certain distance. Generally, the effective processing distance is 1000 times the nozzle diameter. Furthermore, even if there are slight changes in the working distance, processing can continue without adjustment—a capability that traditional lasers cannot achieve.

3.2. Stealth Dicing Technology

Traditional laser cutting focuses laser energy on the wafer surface. However, the introduction of a heat-affected zone (HAZ) leads to increased dicing width and uncontrollable microcracks, which reduce the dicing quality and efficiency of the wafer. One solution to this problem is to use laser irradiation to induce thermal shock inside the wafer, forming controllable cracking, and then apply external force to achieve the cutting effect. This process is the Stealth Dicing Technology (SDT), which was invented and patented by Hamamatsu Corporation.

The basic principle of stealth dicing is shown in Fig.3[18]: a laser emits a laser beam with a specific wavelength, which is focused inside the wafer through a high numerical aperture (NA) lens to form a selective modification layer—known as the stealth dicing (SD) layer. This layer serves as the initiation point for subsequent wafer dicing cracks. By optimizing the laser and optical path system, these initiation points can be confined inside the wafer without causing thermal damage to the front and back surfaces of the semiconductor wafer. External force is then applied to propagate these cracks to the front and back surfaces, thereby separating the wafer into small chips.

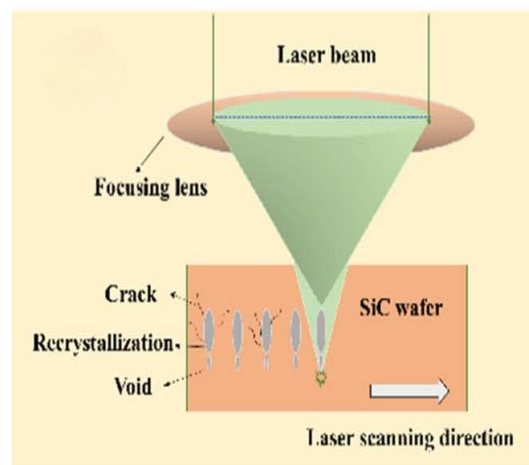


Fig 3. Schematic Diagram of Stealth Dicing

The general process of stealth dicing consists of four steps: front side wafer taping, laser scanning, wafer expanding, and ultraviolet (U-V) irradiation. To summarize: laser scanning is performed from the backside of the wafer, avoiding the front-side pattern damage that may occur due to front-side focusing in traditional laser technology. The number of laser scans varies depending on the wafer thickness, and each scan acts on a different depth of the wafer's backside. The ablation depth of a single laser scan is approximately 25 μm ; thus, a wafer with a thickness of 150 μm requires 3–4 scans. After each scan, an SD layer remains inside the wafer, and microcracks are also generated along the positive and negative directions of the SD layer—these microcracks are key factors promoting wafer separation. In the wafer expanding step, the chips are separated by stretching the expansion tape attached to the wafer surface. Finally, UV irradiation is used to remove the tape from the chip surface.

completing the chip dicing process.

4. Conclusions

This study focused on the high-precision dicing requirements of hard and brittle transparent materials (e.g., silicon wafers, quartz glass) and systematically reviewed the research status of laser cutting technology from three aspects: traditional dicing, assisted dicing, and dicing after spatial light modulation (SLM), while analyzing key influencing factors (laser type, polarization state, processing parameters).

Traditional cutting technologies show both maturity and limitations. Tool-based cutting, a mature process in the semiconductor industry, struggles with ultra-thin wafers ($<100\text{ }\mu\text{m}$) (e.g., chipping, residual stress) and faces coolant-related cost and environmental issues. Traditional laser cutting (e.g., CO_2 , Nd:YAG lasers) improves speed and wafer utilization but cannot eliminate thermal effects, leading to heat affected zone (HAZ) and microcracks.

New laser cutting technologies achieve critical breakthroughs. Micro-water-jet guided laser cutting controls HAZ to the micron level via laser-water jet coupling, suitable for ultra-thin wafers. Stealth Dicing Technology (SDT) forms internal modified layers for stress-controlled separation, enhancing wafer utilization by 15%-20% without coolant pollution. These technologies effectively address the bottlenecks of traditional methods for hard and brittle material dicing.

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